

(19) World Intellectual Property
Organization
International Bureau



(43) International Publication Date
3 February 2005 (03.02.2005)

PCT

(10) International Publication Number
WO 2005/010944 A2

(51) International Patent Classification⁷: **H01L**

(21) International Application Number:
PCT/US2004/023183

(22) International Filing Date: 19 July 2004 (19.07.2004)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
10/626,760 21 July 2003 (21.07.2003) US

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(81) Designated States (unless otherwise indicated, for every kind of national protection available): AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NA, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW.

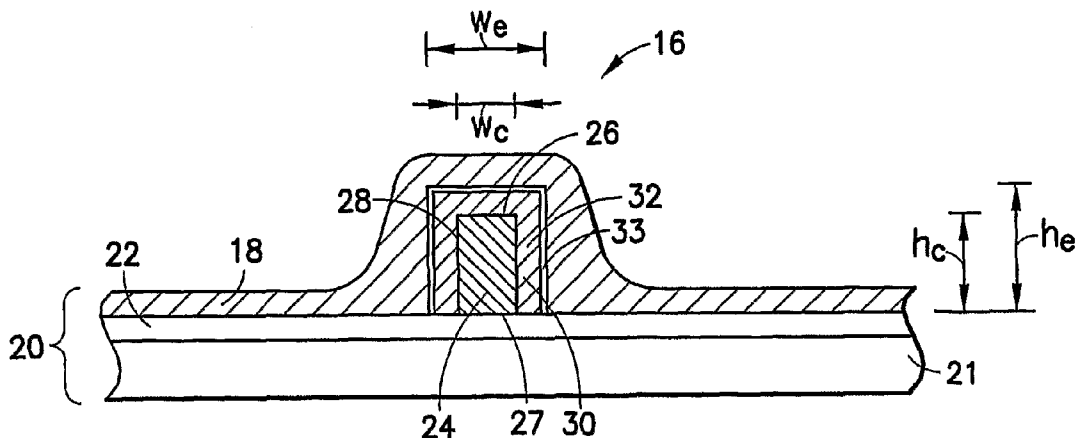
(84) Designated States (unless otherwise indicated, for every kind of regional protection available): ARIPO (BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IT, LU, MC, NL, PL, PT, RO, SE, SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Published:

— without international search report and to be republished upon receipt of that report

For two-letter codes and other abbreviations, refer to the "Guidance Notes on Codes and Abbreviations" appearing at the beginning of each regular issue of the PCT Gazette.

(54) Title: FET CHANNEL HAVING A STRAINED LATTICE STRUCTURE ALONG MULTIPLE SURFACES



(57) Abstract: A channel (16) of a FinFET (10) has a channel core (24) and a channel envelope (32), each made from a semiconductor material defining a different lattice structure to exploit strained silicon properties. A gate is coupled to the channel envelope through a gate dielectric. Exemplary materials are Si and Si_xGe_{1-x}, wherein 78<x<92. The channel core (24) has a top surface (26) of width w_c and an upstanding surface (28, 30) of height h_c, preferably oriented 90° to one another. The channel envelope (32) is in contact with the top (26) and upstanding surfaces (28, 30), so that the area of interface is increased as compared to contact only along the top surface (26), improving electrical conductivity and gate (18) control over the channel (16). The height h_c can be tailored to enable a smaller scale FET (10) within a stabilized SRAM. Various methods of making the channel (16) are disclosed, including a mask and etch method, a handle wafer/carrier wafer method, and a shallow trench method. Embodiments and methods for FinFETs with one to four gates are disclosed.

WO 2005/010944 A2